



900V Super-junction Power MOSFET

Description

900V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The deep trench SJ MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

Features

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Low Power Chargers and Adapters

TO-220F



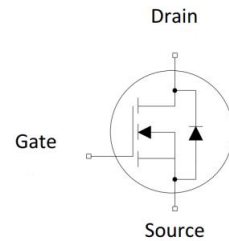
TO-263



TO-220



TO-247



Device Marking and Package Information

Device	Package	Marking
TPA90R350A	TO-220F	90R350A
TPB90R350A	TO-263	90R350A
TPP90R350A	TO-220	90R350A
TPW90R350A	TO-247	90R350A

Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	950	V
$R_{DS(on),max}$	0.35	Ω
$Q_{g,typ}$	62	nC
I_D	15	A
$I_{D,pulse}$	45	A



Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, unless otherwise noted				
Parameter		Symbol	Values	Unit
Continuous Drain Current	$T_C = 25^{\circ}\text{C}$	I_D	15	A
	$T_C = 100^{\circ}\text{C}$		9	
Pulsed Drain Current	(note1)	$I_{D,pulse}$	45	A
Gate-Source Voltage		V_{GSS}	$\pm 30\text{V}$	V
Single Pulse Avalanche Energy	(note2)	E_{AS}	280	mJ
Repetitive Avalanche Energy	(note2)	E_{AR}	0.5	mJ
Avalanche Current		I_{AR}	7.5	A
Power Dissipation For TO-220F		P_D	34	W
Power Dissipation For TO-263, TO-220, TO-247			240	
Continuous Diode Forward Current		I_S	15	A
Diode Pulsed Current	(note1)	$I_{S,pulse}$	45	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	$-55 \sim +150$	$^{\circ}\text{C}$

Thermal Resistance For TO-220F			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	3.67	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Thermal Resistance For TO-263, TO-220, TO-247			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.52	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	



Electrical Characteristics T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	900	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 900V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
		V _{DS} = 900V, V _{GS} = 0V, T _J = 150°C	--	--	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.5	--	4.5	V
Drain-Source On-State-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 7.5A	--	0.31	0.35	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1.0MHz	--	2840	--	pF
Output Capacitance	C _{oss}		--	220	--	
Reverse Transfer Capacitance	C _{rss}		--	16	--	
Total Gate Charge	Q _g	V _{DD} = 720V, I _D = 15A, V _{GS} = 10V	--	62	--	nC
Gate-Source Charge	Q _{gs}		--	15	--	
Gate-Drain Charge	Q _{gd}		--	23	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 400V, I _D = 15A, R _G = 25Ω	--	49	--	ns
Turn-on Rise Time	t _r		--	42	--	
Turn-off Delay Time	t _{d(off)}		--	166	--	
Turn-off Fall Time	t _f		--	13	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V _{SD}	T _J = 25°C, I _{SD} = 15A, V _{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t _{rr}	V _R = 400V, I _F = I _S , di _F /dt = 100A/μs	--	680	--	ns
Reverse Recovery Charge	Q _{rr}		--	9	--	μC
Peak Reverse Recovery Current	I _{rrm}		--	24	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_D = 10A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical R_G



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

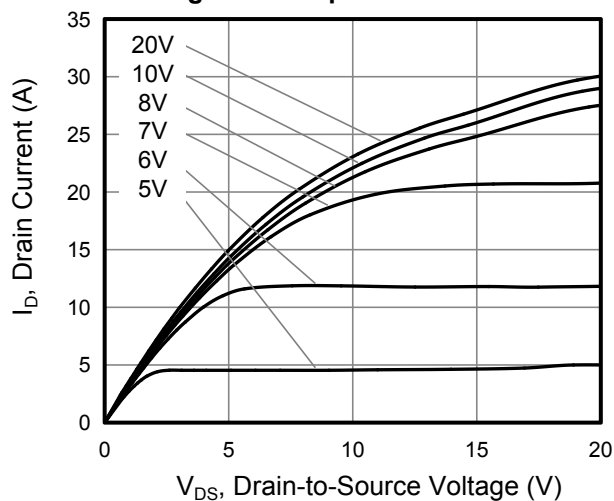


Figure 2. Transfer Characteristics

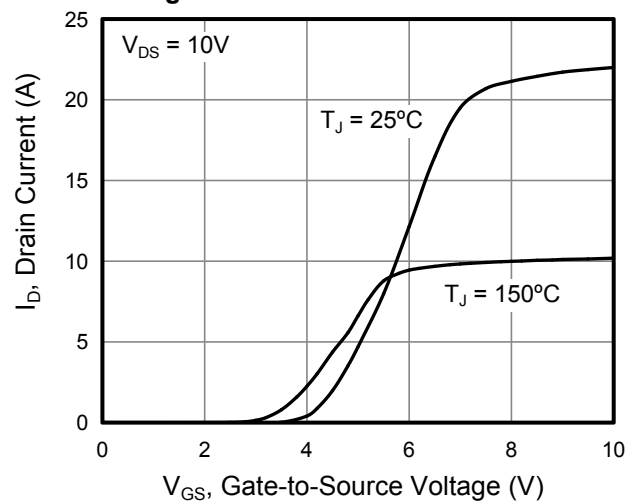


Figure 3. On-Resistance vs. Drain Current

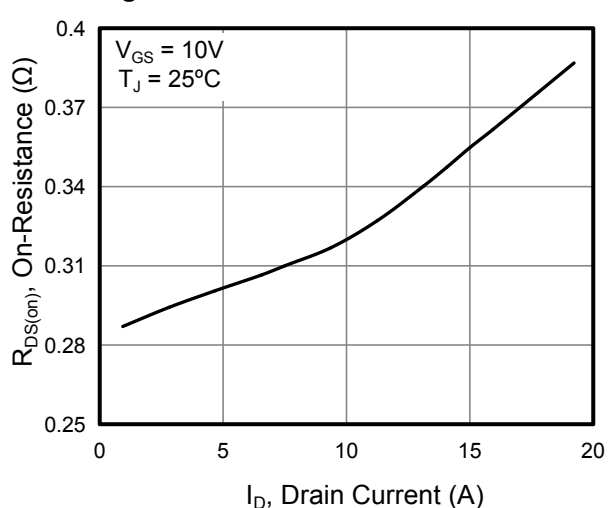


Figure 4. Capacitance

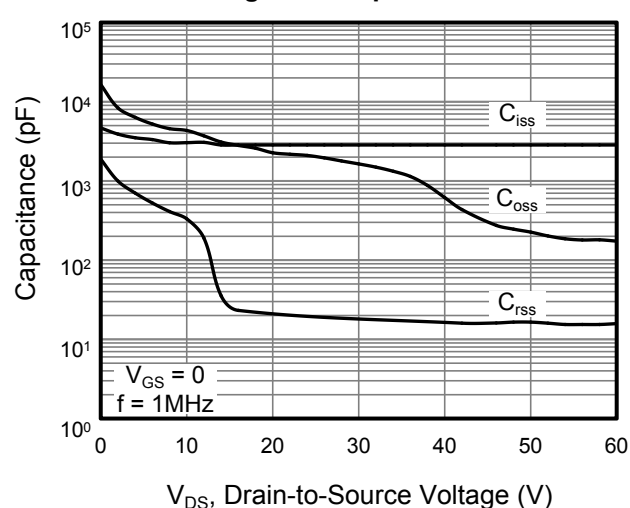


Figure 5. Gate Charge

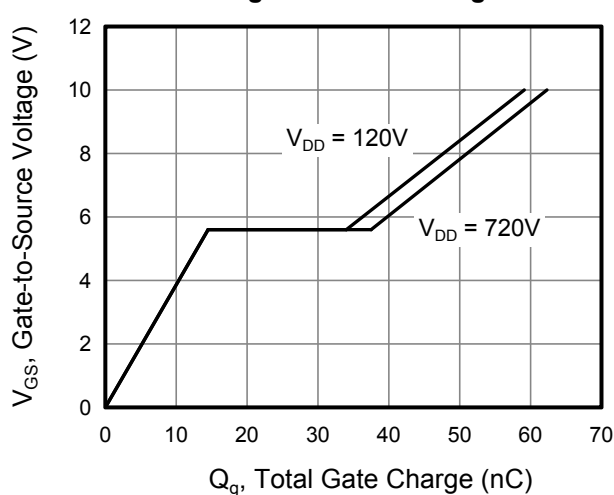
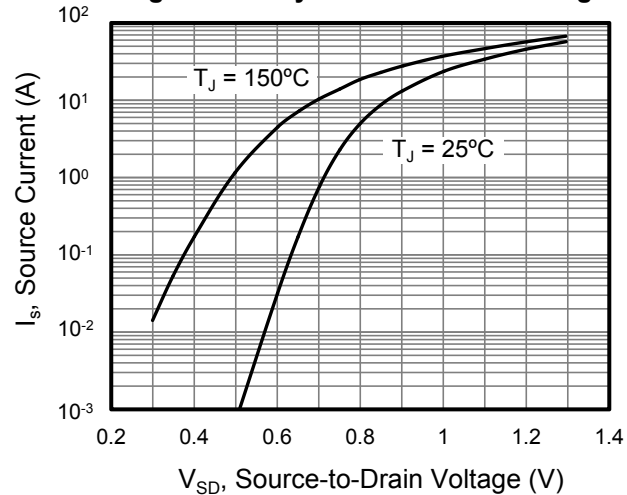


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

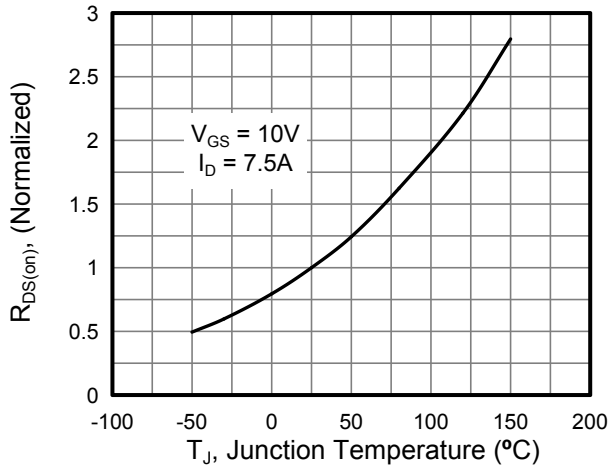


Figure 8. Threshold Voltage vs. Junction Temperature

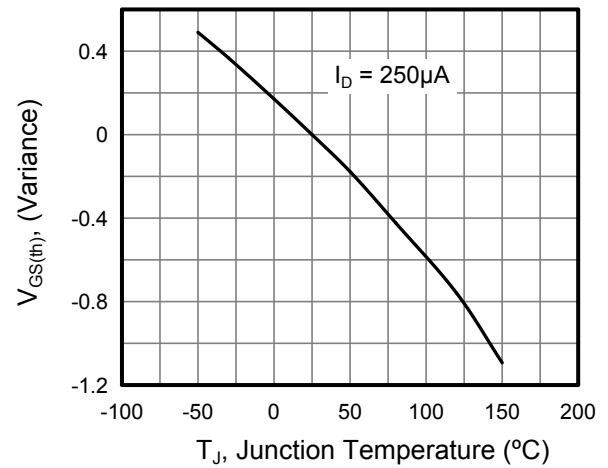


Figure 9. Transient Thermal Impedance For TO-220F

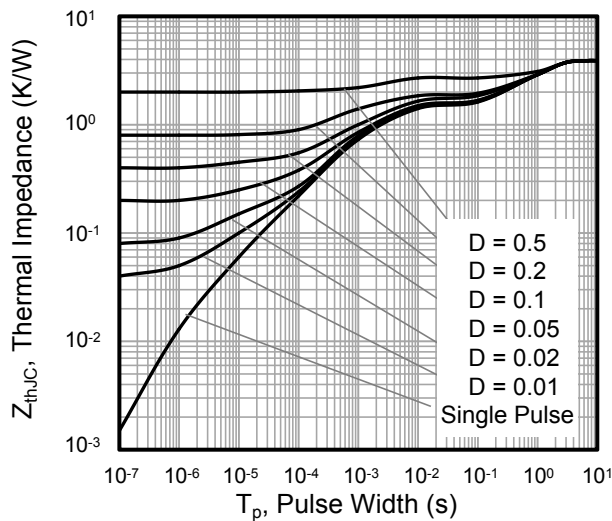


Figure 10. Transient Thermal Impedance For TO-263/TO-220/TO-247

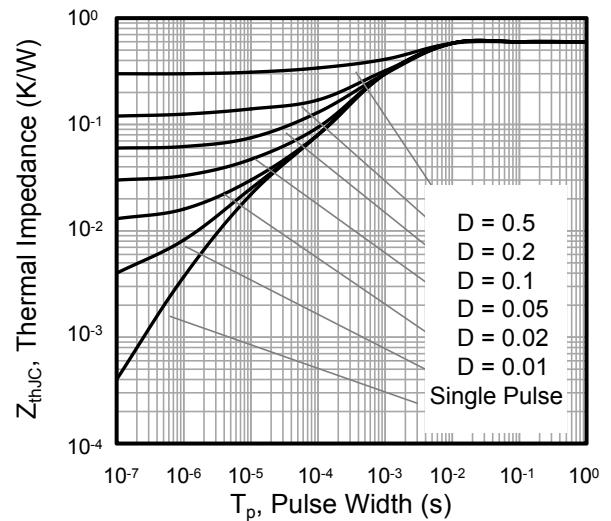


Figure 11. Safe Operation Area For TO-220F

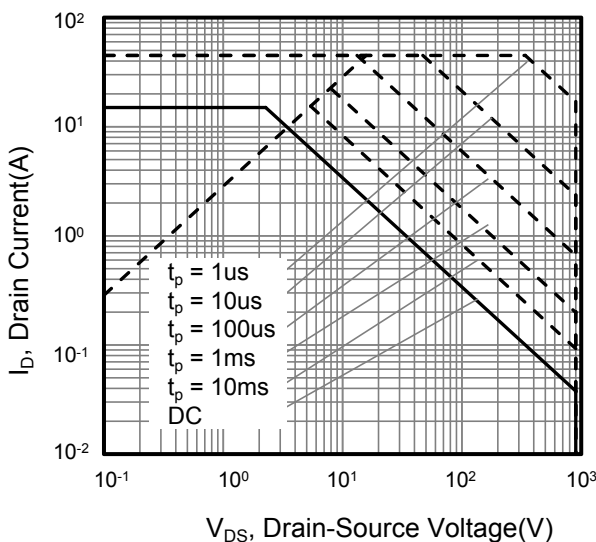


Figure 12. Safe Operation Area For TO-263/TO-220/TO-247

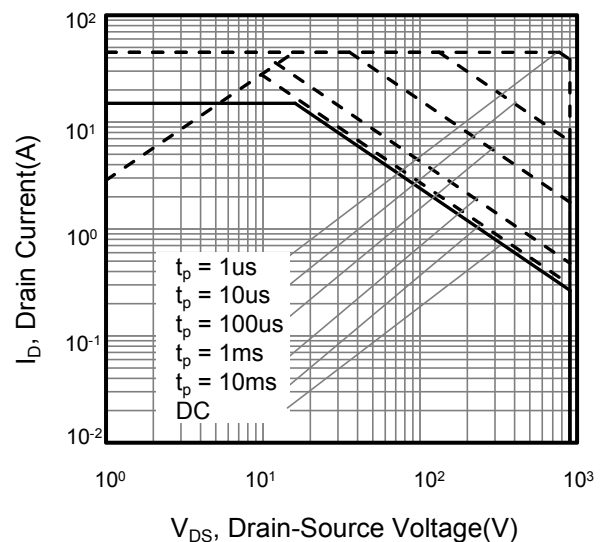




Figure A: Gate Charge Test Circuit and Waveform

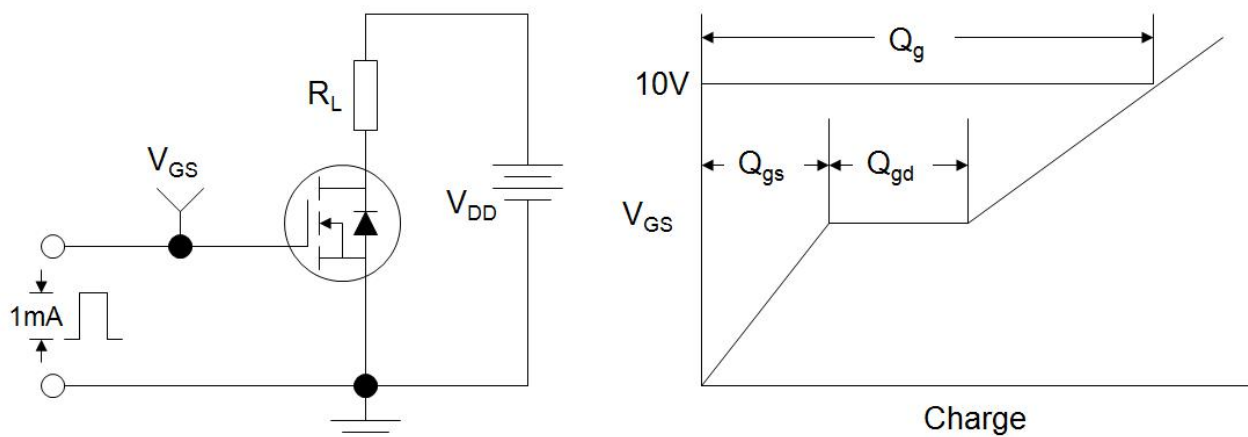


Figure B: Resistive Switching Test Circuit and Waveform

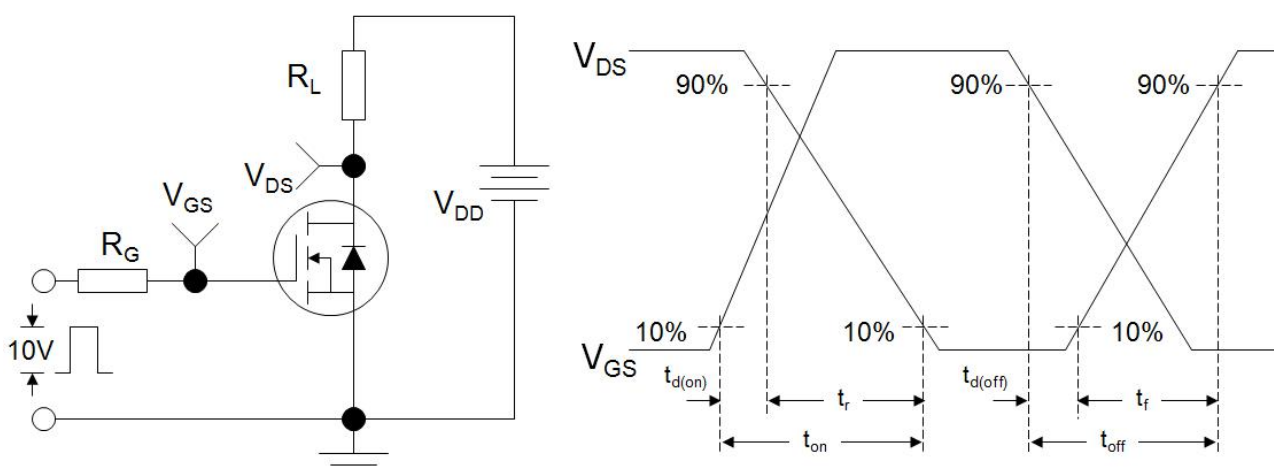
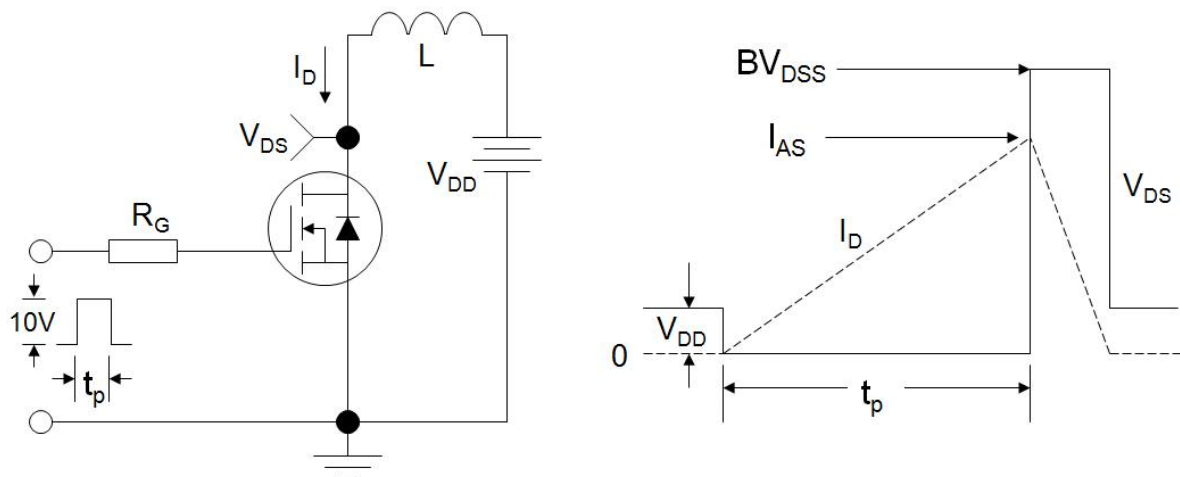
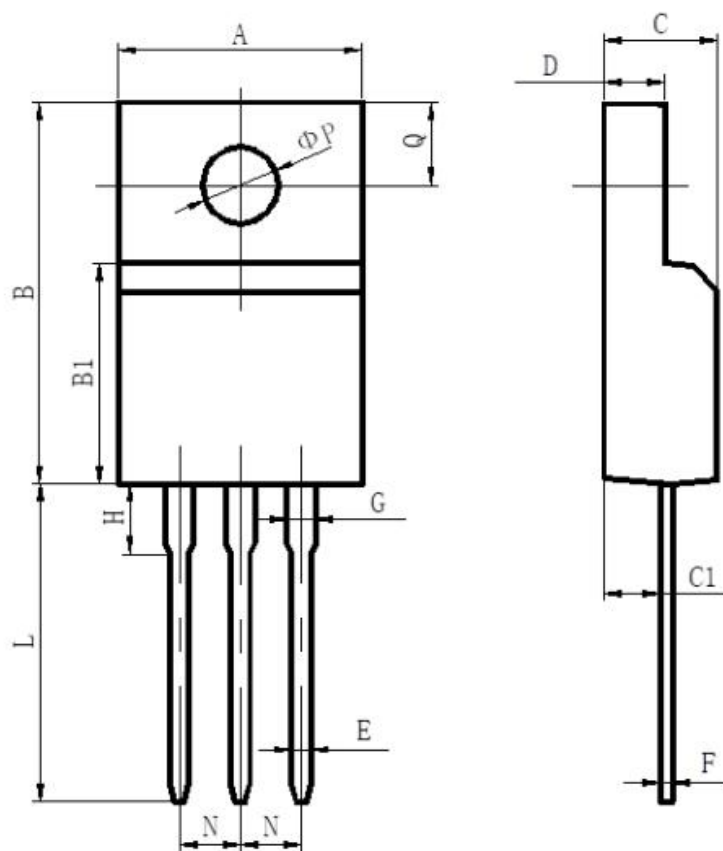


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





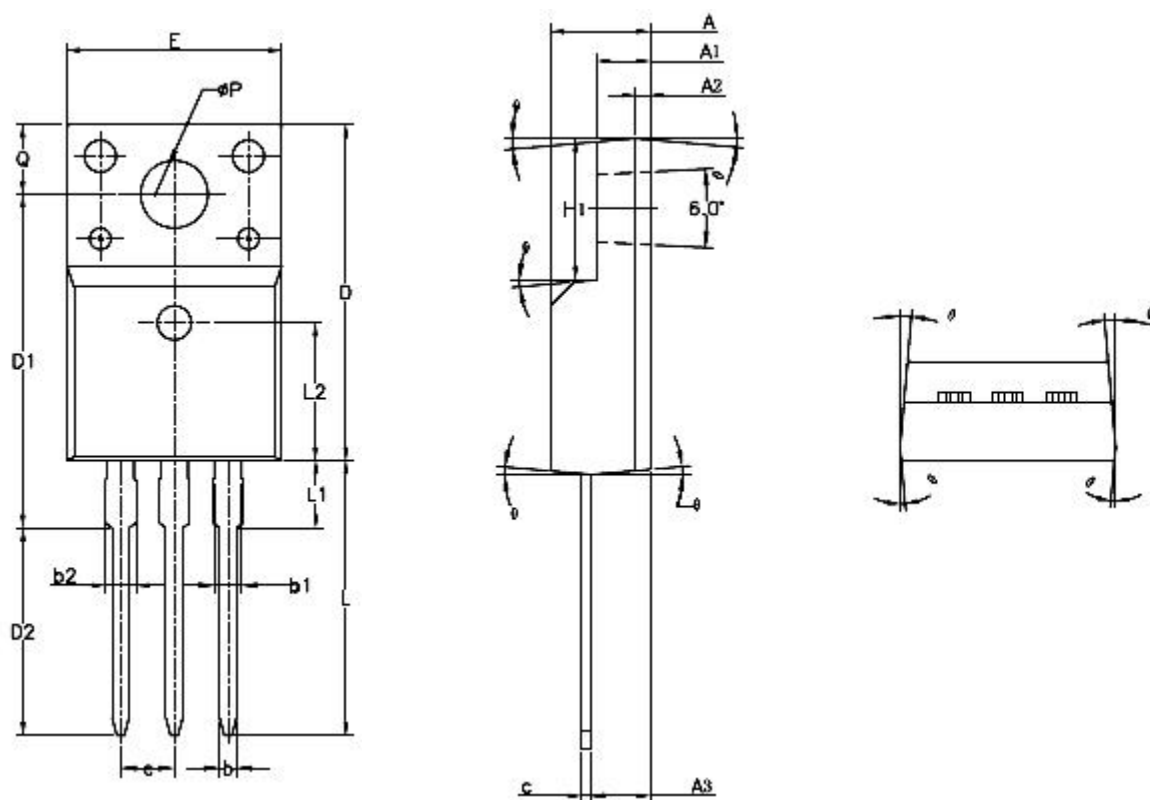
TO-220F（海天）



项目	规范(mm)	
	MIN	MAX
A	9.70	10.30
B	15.50	16.10
B1	8.99	9.39
C	4.40	4.80
C1	2.15	2.55
D	2.50	2.90
E	0.70	0.90
F	0.40	0.60
G	1.12	1.42
H	3.40	3.80
L	12.6	13.6
N	2.34	2.74
Q	3.15	3.55
Φ P	3.00	3.30



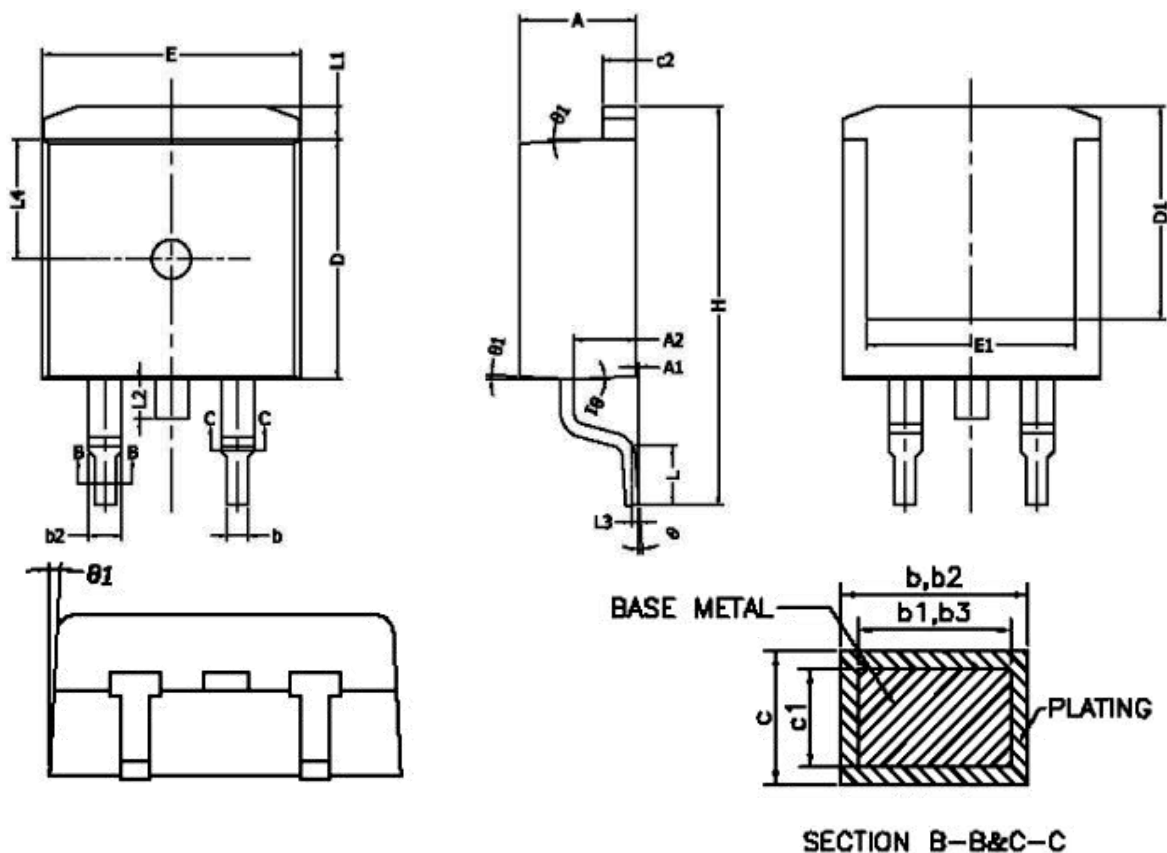
TO-220F (集佳)



SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2	0.70 REF		
A3	2.56	2.76	2.93
b	0.70	—	0.90
b1	1.18	—	1.38
b2	—	—	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.0
E	9.96	10.16	10.36
e	2.54BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	—	—	3.50
L2	6.50REF		
øP	3.08	3.18	3.28
Q	3.20	—	3.40
θ1	1°	3°	5°



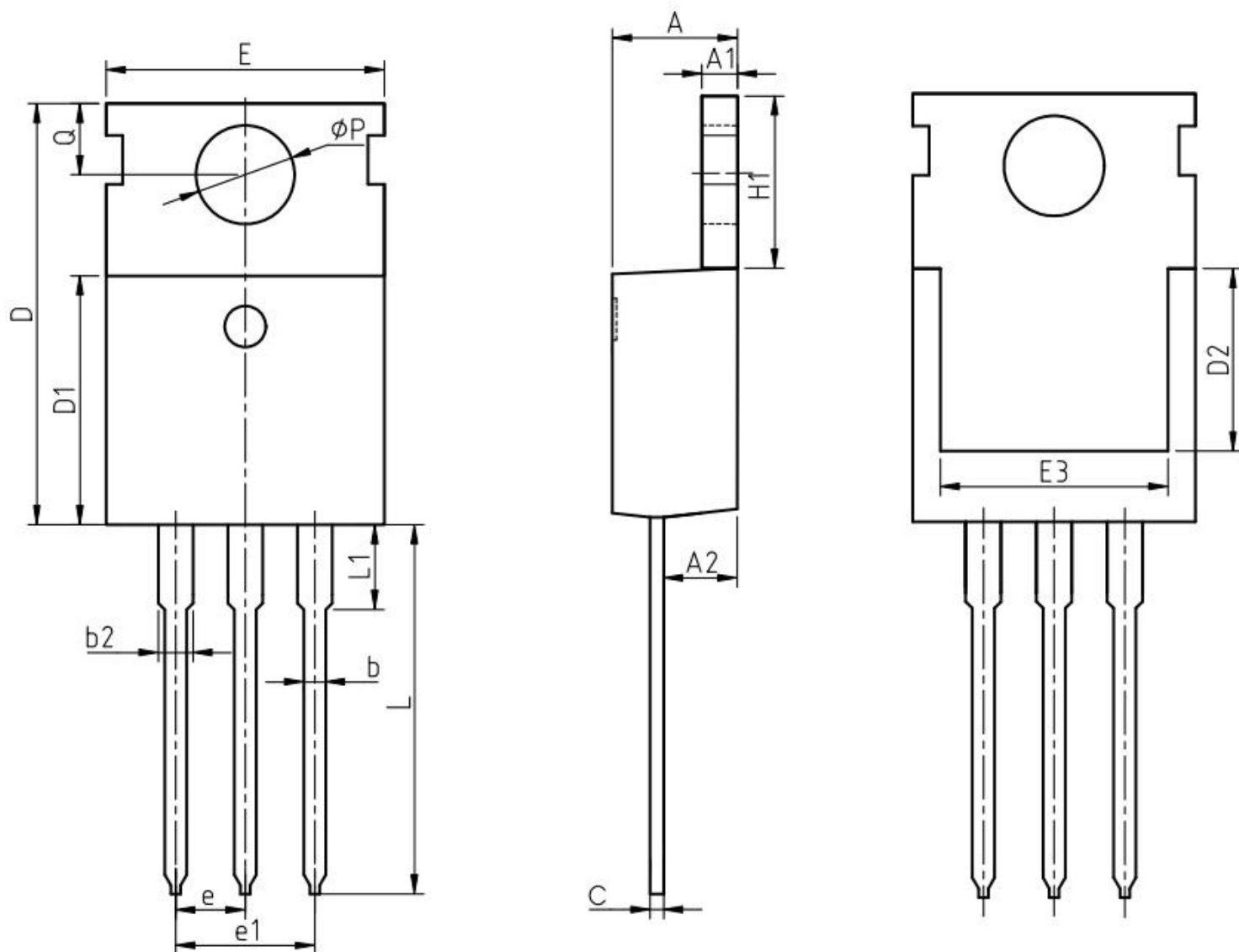
TO-263 (集佳)



SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	---	---	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	---	8°
θ1	1°	3°	5°



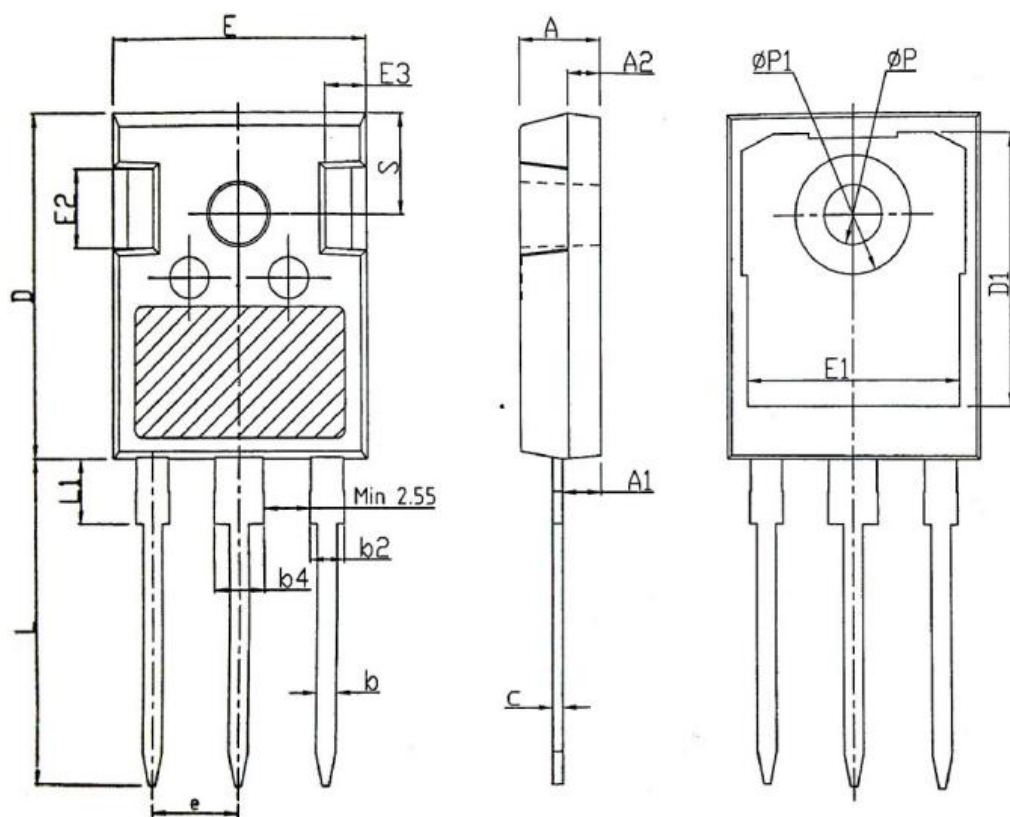
TO-220 (华羿)



Unit:mm				Unit:mm			
Symbol	Min.	Nom	Max.	Symbol	Min.	Nom	Max.
A	4.37	4.57	4.70	E	9.70	10.00	10.30
A1	1.25	1.30	1.40	E3	7.00	-	-
A2	2.20	2.40	2.60	e	2.54 BSC		
b	0.70	0.80	0.95	e1	5.08 BSC		
b2	1.17	1.27	1.47	H1	6.25	6.50	6.85
c	0.45	0.50	0.60	L	12.75	13.50	13.80
D	15.10	15.60	16.10	L1	-	3.10	3.40
D1	8.80	9.10	9.40	ΦP	3.40	3.60	3.80
D2	5.50	-	-	Q	2.60	2.80	3.00



TO-247 (华羿)



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15BSC		



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